

## NCE N-Channel Super Trench Power MOSFET



The NCEP02515K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **General Features**

• V<sub>DS</sub> =250V,I<sub>D</sub> =15A

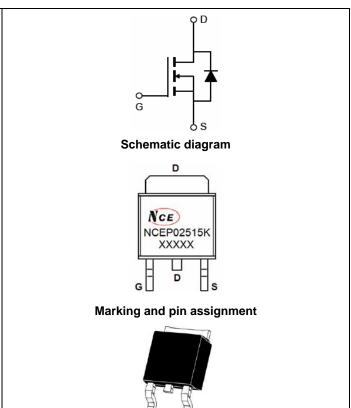
R<sub>DS(ON)</sub>=200mΩ (typical) @ V<sub>GS</sub>=10V

- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

#### Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

#### 100% UIS TESTED!



TO-252 -2Ltop view

### Package Marking and Ordering Information

	<u> </u>	V			
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02515K	NCEP02515K	TO-252-2L	-	-	-

## Absolute Maximum Ratings (T<sub>A</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	250	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	ID	15	А
Drain Current-Continuous(T <sub>C</sub> =100 ℃)	I <sub>D</sub> (100℃)	10.6	A
Pulsed Drain Current	I <sub>DM</sub>	60	A
Maximum Power Dissipation	PD	140	W
Derating factor		0.93	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	80	mJ
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C

#### Thermal Characteristic

Thermal Résistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	1.1	°C <b>/W</b>	
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## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	· ·		•	•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	250	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =250V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)	· ·		•	•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =10V, I <sub>D</sub> =15A	-	200	220	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =15A	15	-	-	S
Dynamic Characteristics (Note4)	· ·		•	•		
Input Capacitance	C <sub>lss</sub>		-	475		PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =125V,V <sub>GS</sub> =0V, F=1.0MHz	-	34		PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	1.2		PF
Switching Characteristics (Note 4)	· ·		•	•		
Turn-on Delay Time	t <sub>d(on)</sub>		-	4	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =125V, R∟=8Ω	-	5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_G$ =3 $\Omega$	-	10	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	2	-	nS
Total Gate Charge	Qg		-	8.9	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =125V,I <sub>D</sub> =15A, V <sub>GS</sub> =10V	-	3.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =15A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	15	А
Reverse Recovery Time	t <sub>rr</sub>	$T_J$ = 25°C, $I_F$ = $I_S$	-	25	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	110	-	nC

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board,  $t \le 10$  sec.

3. Pulse Test: Pulse Width ≤ 300 $\mu$ s, Duty Cycle ≤ 2%.

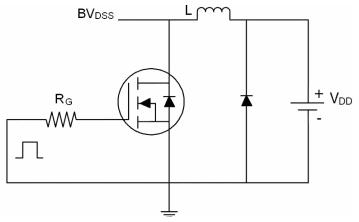
4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25  $^\circ \!\! \mathbb{C}$  ,V\_{DD}=50V,V\_G=10V,L=0.5mH,Rg=25\Omega

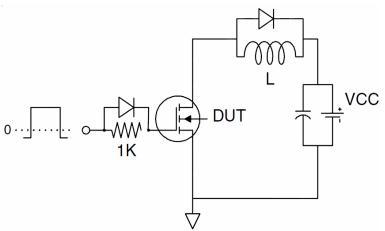


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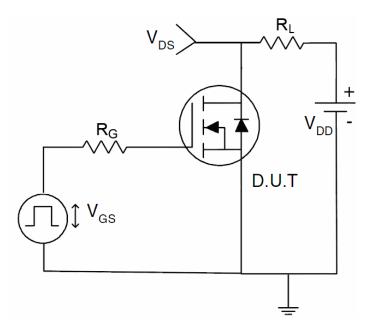
## Test Circuit 1) E<sub>AS</sub> test Circuit



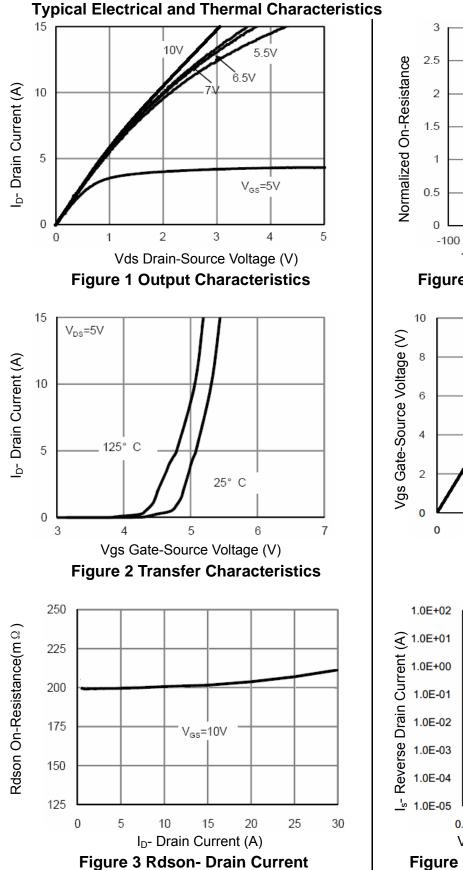
### 2) Gate charge test Circuit



3) Switch Time Test Circuit







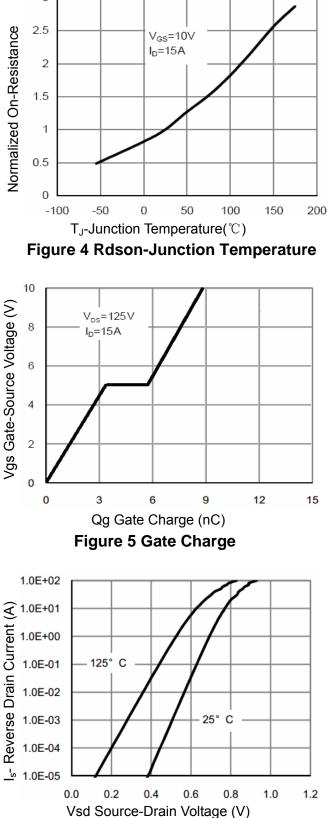


Figure 6 Source- Drain Diode Forward



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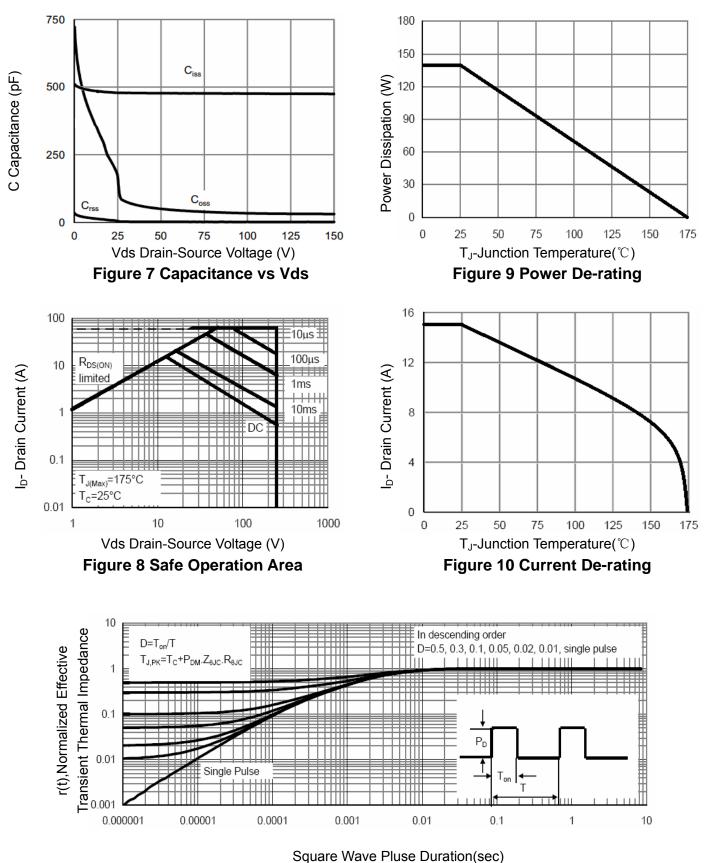
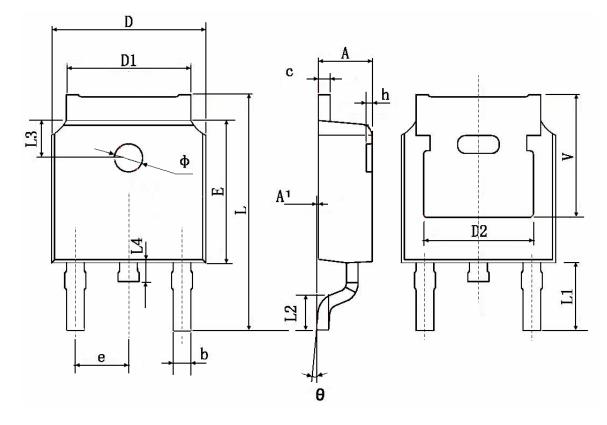


Figure 11 Normalized Maximum Transient Thermal Impedance



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## **TO-252 Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.	4.830 TYP.		TYP.	
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.90	2.900 TYP.		TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063	B TYP.	
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.35	0 TYP.	0.211 TYP.		



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